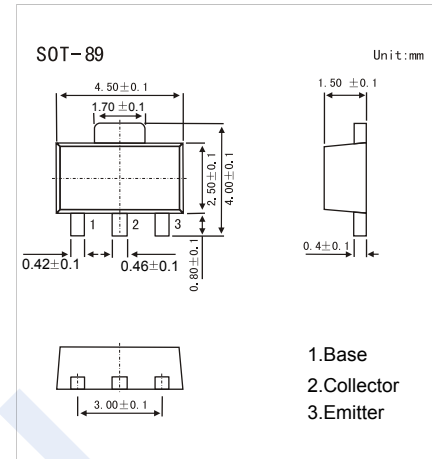


## PNP Transistors

### 2SB1027

#### ■ Features

- Low frequency power amplifier



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	-180	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-120	
Emitter - Base Voltage	V <sub>EBO</sub>	-5	
Collector Current - Continuous	I <sub>C</sub>	-1.5	A
Collector current -Pulse (Note.1)	I <sub>CP</sub>	-3	
Collector Power Dissipation	P <sub>C</sub>	1	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

Note.1: PW ≤ 10ms, Duty cycle ≤ 20%

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = -1mA, I <sub>E</sub> = 0	-180			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -10mA, R <sub>BE</sub> = ∞	-120			
Emitter - base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -1mA, I <sub>C</sub> = 0	-5			
Collector-base cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -160V, I <sub>E</sub> = 0			-10	uA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0			-0.1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-1	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-1.2	
Base - emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -150 mA			-0.9	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -150 mA	60		320	
		V <sub>CE</sub> = -5V, I <sub>C</sub> = -500 mA	30			

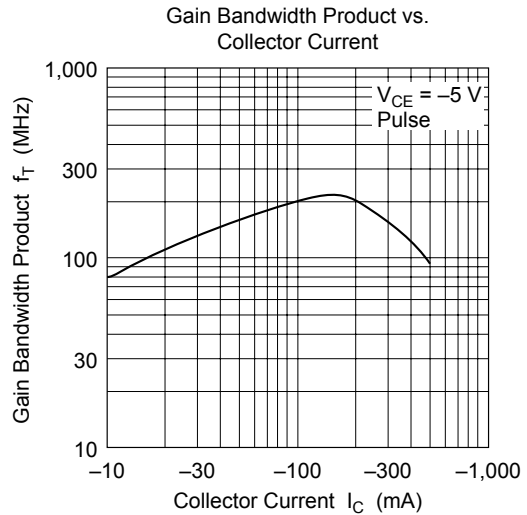
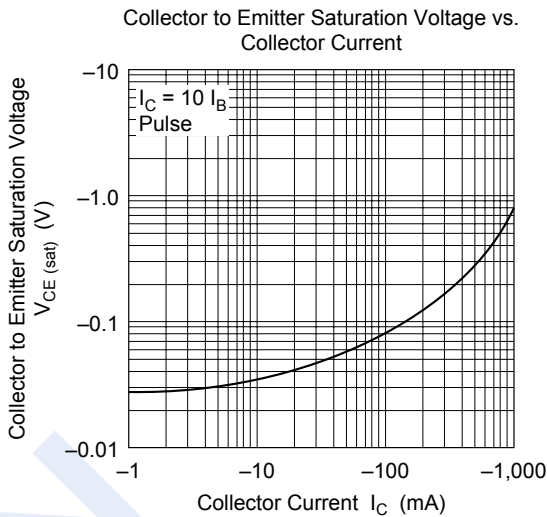
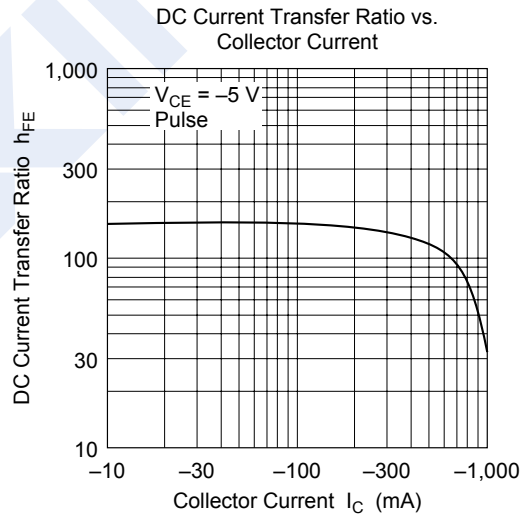
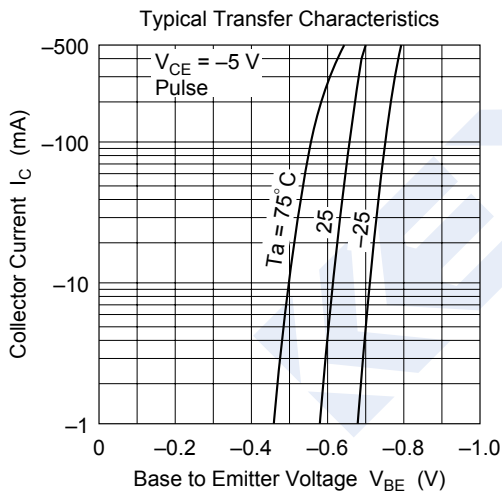
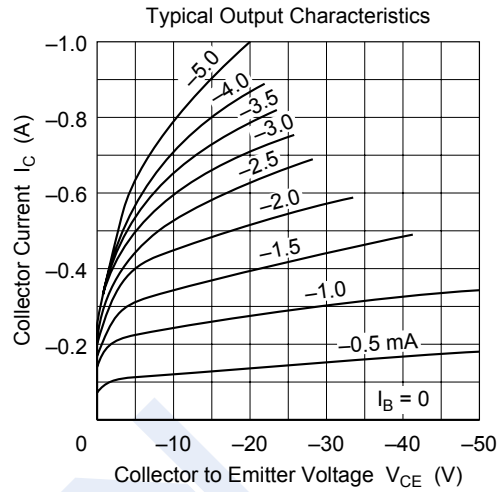
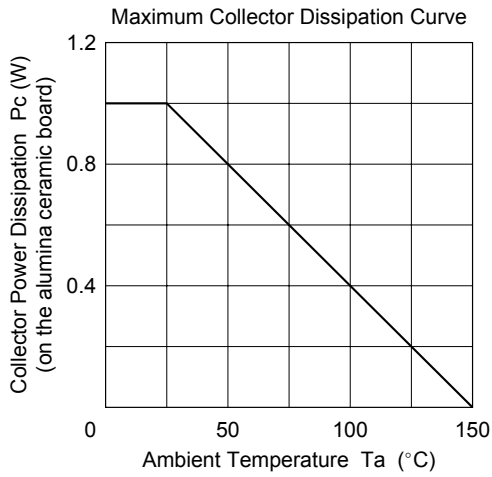
#### ■ Classification of h<sub>FE</sub>(1)

Type	2SB1027-H	2SB1027-J	2SB1027-K
Range	60-120	100-200	160-320
Marking	EH	EJ	EK

# PNP Transistors

## 2SB1027

■ Typical Characteristics



## PNP Transistors

## 2SB1027

## ■ Typical Characteristics

